

Silicon Carbide (SiC) MOSFET – 80 mohm, 1200 V, M1, Bare Die NTC080N120SC1

Description

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

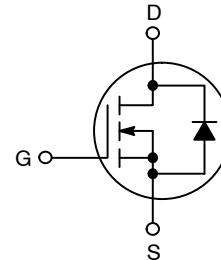
- 1200 V @ $T_J = 175^\circ\text{C}$
- Typ $R_{DS(on)} = 80\text{ m}\Omega$ at $V_{GS} = 20\text{ V}$, $I_D = 20\text{ A}$
- High Speed Switching with Low Capacitance
- 100% UIL Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Applications

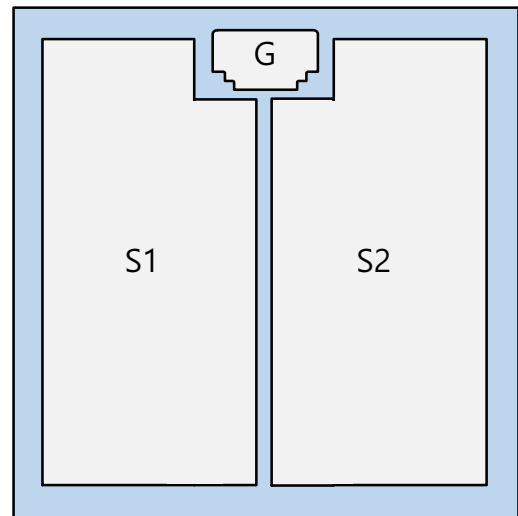
- Industrial Motor Drive
- UPS
- Boost Inverter
- PV Charger

$V_{(BR)DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
1200 V	110 m Ω @ 20 V	31 A

N-CHANNEL MOSFET



DIE DIAGRAM

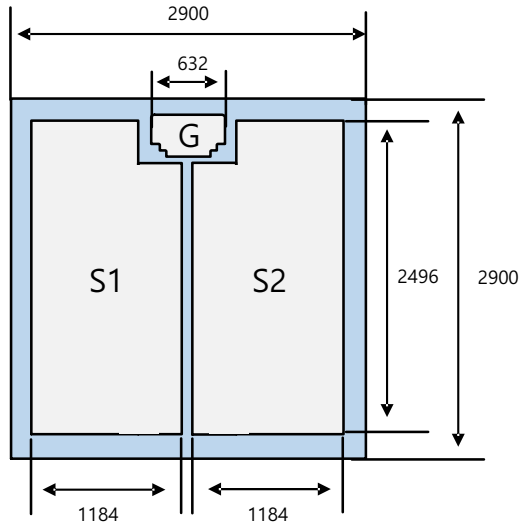


Die Information

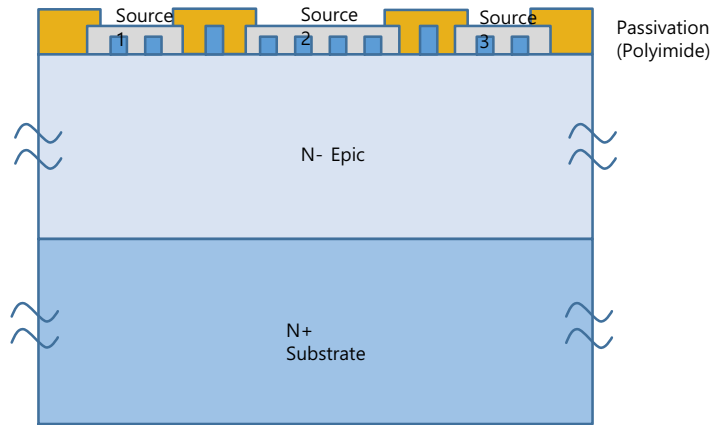
• Wafer Diameter	6 inch
• Die Size	2,900 x 2,900 μm
• Metallization	
· Top	Ti/TiN/Al 5 μm
· Back	Ti/V/Ni/Ag
• Die Thickness	Typ. 200 μm
• Gate Pad Size	632 x 242.5 μm

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Die Layout



Die Cross Section



Passivation Information

- Passivation Material: Polyimide (PSPi)
- Passivation Type: Local Passivation
- Passivation Thickness 10 μm
- : Passivation Area

Die Layout

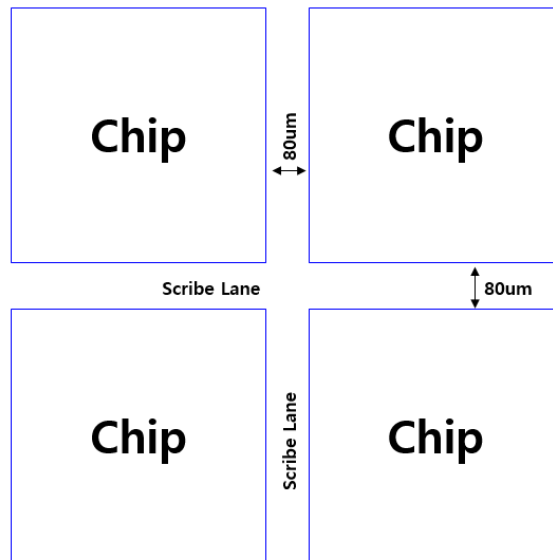


Figure 1. Bare Die Dimensions

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MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	1200	V
Gate-to-Source Voltage			V _{GS}	−15/+25	V
Recommended Operation Values of Gate-to-Source Voltage	T _C < 175°C		V _{GSop}	−5/+20	V
Continuous Drain Current R _{θJC}	Steady State	T _C = 25°C	I _D	31	A
Power Dissipation R _{θJC}			P _D	178	W
Continuous Drain Current R _{θJC}	Steady State	T _C = 100°C	I _D	22	A
Power Dissipation R _{θJC}			P _D	89	W
Pulsed Drain Current (Note 2)	T _C = 25°C		I _{DM}	132	A
Single Pulse Surge Drain Current Capability	T _C = 25°C, t _p = 10 μs, R _G = 4.7 Ω		I _{DSC}	132	A
Operating Junction and Storage Temperature Range			T _J , T _{stg}	−55 to +175	°C
Source Current (Body Diode)			I _S	18	A
Single Pulse Drain-to-Source Avalanche Energy (I _{L(pk)} = 18.5 A, L = 1 mH) (Note 3)			E _{AS}	171	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Note 1)	R _{θJC}	0.84	°C/W

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 171 mJ is based on starting T_J = 25°C; L = 1 mH, I_{AS} = 18.5 A, V_{DD} = 120 V, V_{GS} = 18 V.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	1200	–	–	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = 1 mA, referenced to 25°C	–	700	–	mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 1200 V, T _J = 25°C	–	–	100	μA
		V _{GS} = 0 V, V _{DS} = 1200 V, T _J = 175°C	–	–	250	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = +25/-15 V, V _{DS} = 0 V	–	–	±1	μA

ON CHARACTERISTICS

Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 5 mA	1.8	2.7	4.3	V
Recommended Gate Voltage	V _{GOP}		–5	–	+20	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 20 V, I _D = 20 A, T _J = 25°C	–	80	110	mΩ
		V _{GS} = 20 V, I _D = 20 A, T _J = 150°C	–	114	–	
Forward Transconductance	g _{FS}	V _{DS} = 20 V, I _D = 20 A	–	13	–	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 800 V	–	1112	–	pF
Output Capacitance	C _{OSS}		–	80	–	
Reverse Transfer Capacitance	C _{RSS}		–	6.5	–	
Total Gate Charge	Q _{G(tot)}	V _{GS} = –5/20 V, V _{DS} = 600 V, I _D = 20 A	–	56	–	nC
Gate-to-Source Charge	Q _{GS}		–	11	–	
Gate-to-Drain Charge	Q _{GD}		–	12	–	
Gate Resistance	R _G	f = 1 MHz	–	1.7	–	Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	t _{d(on)}	V _{GS} = –5/20 V, V _{DS} = 800 V, I _D = 20 A, R _G = 4.7 Ω, Inductive Load	–	13	–	ns
Rise Time	t _r		–	20	–	
Turn-Off Delay Time	t _{d(off)}		–	22	–	
Fall Time	t _f		–	10	–	
Turn-On Switching Loss	E _{ON}		–	258	–	μJ
Turn-Off Switching Loss	E _{OFF}		–	52	–	
Total Switching Loss	E _{TOT}		–	311	–	

DRAIN-SOURCE DIODE CHARACTERISTICS

Continuous Drain-to-Source Diode Forward Current	I _{SD}	V _{GS} = –5 V	–	–	18	A
Pulsed Drain-to-Source Diode Forward Current (Note 2)	I _{SDM}	V _{GS} = –5 V	–	–	132	A
Forward Diode Voltage	V _{SD}	V _{GS} = –5 V, I _{SD} = 10 A	–	4	–	V
Reverse Recovery Time	t _{RR}	V _{GS} = –5/20 V, I _{SD} = 20 A, dI _S /dt = 1000 A/μs	–	16	–	ns
Reverse Recovery Charge	Q _{RR}		–	62	–	nC
Reverse Recovery Energy	E _{REC}		–	5	–	μJ
Peak Reverse Recovery Current	I _{RRM}		–	8	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

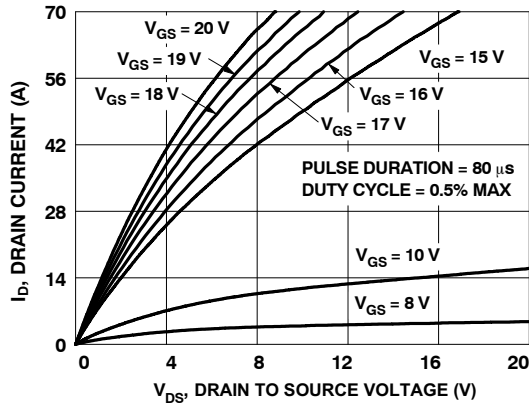


Figure 2. On Region Characteristics

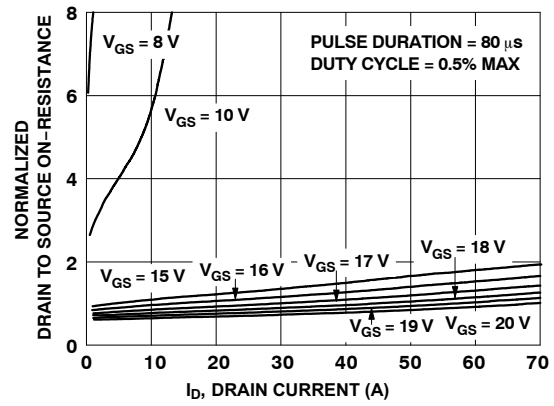


Figure 3. Normalized On-Resistance vs. Drain Current and Gate Voltage

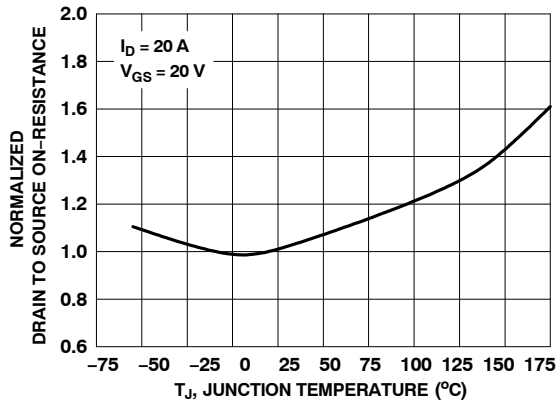


Figure 4. Normalized On Resistance vs. Junction Temperature

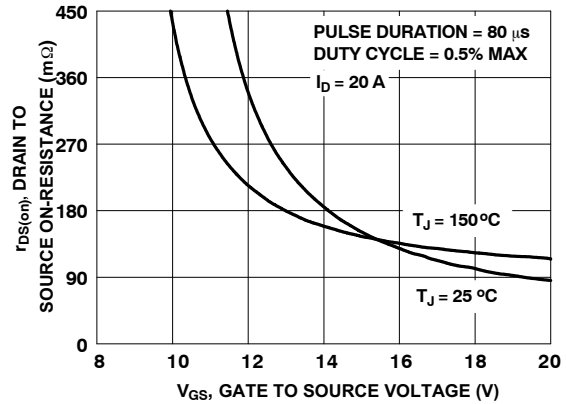


Figure 5. On-Resistance vs. Gate-to-Source Voltage

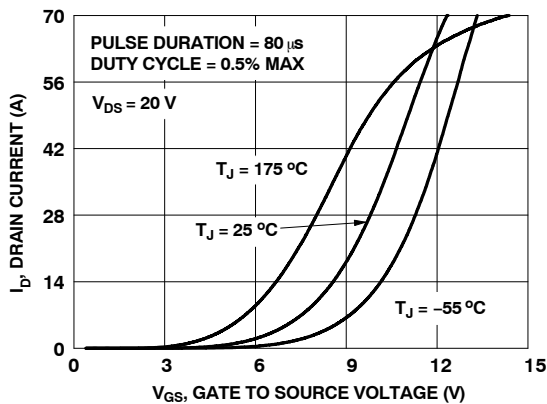


Figure 6. Transfer Characteristics

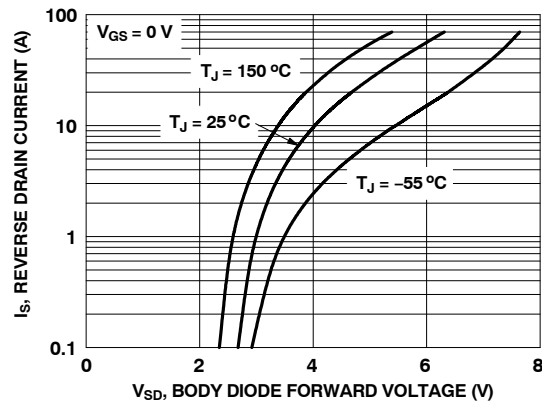


Figure 7. Source-to-Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

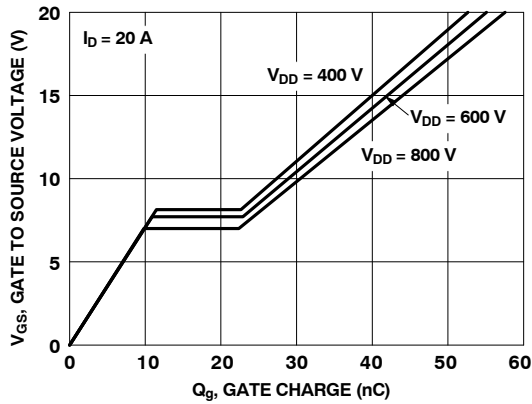


Figure 8. Gate Charge Characteristics

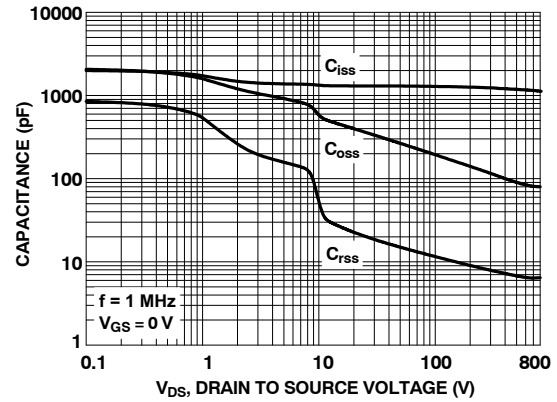


Figure 9. Capacitance vs. Drain-to-Source Voltage

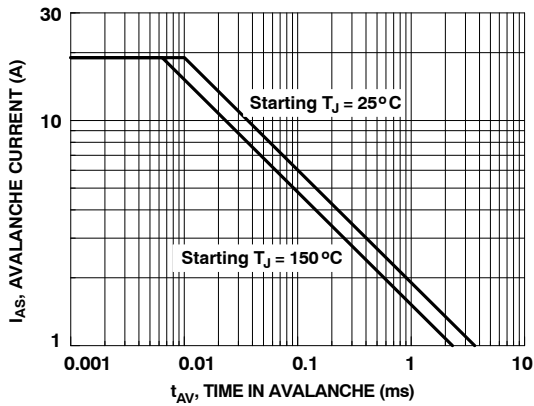


Figure 10. Unclamped Inductive Switching Capability

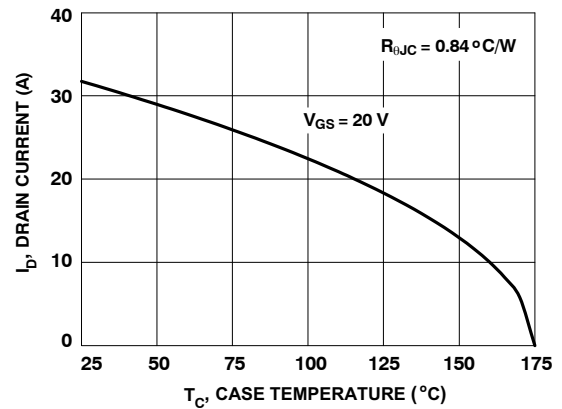


Figure 11. Maximum Continuous Drain Current vs. Case Temperature

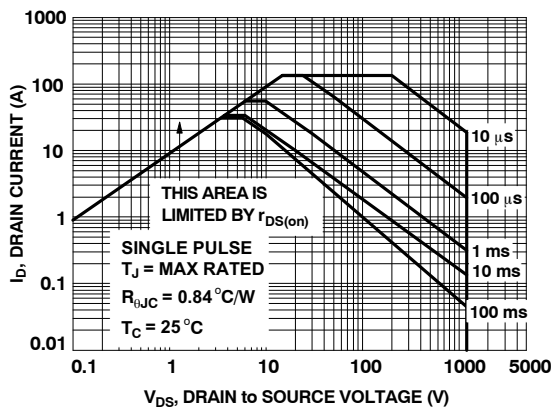


Figure 12. Forward Bias Safe Operating Area

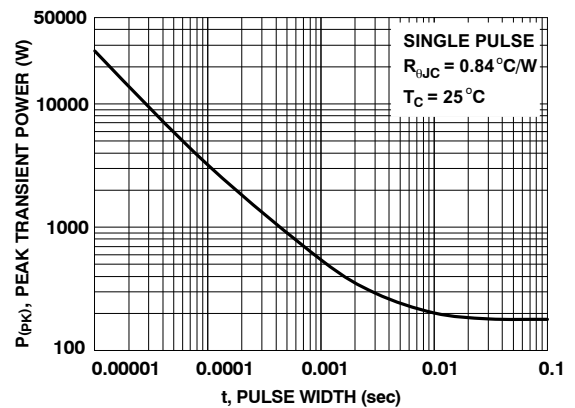


Figure 13. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

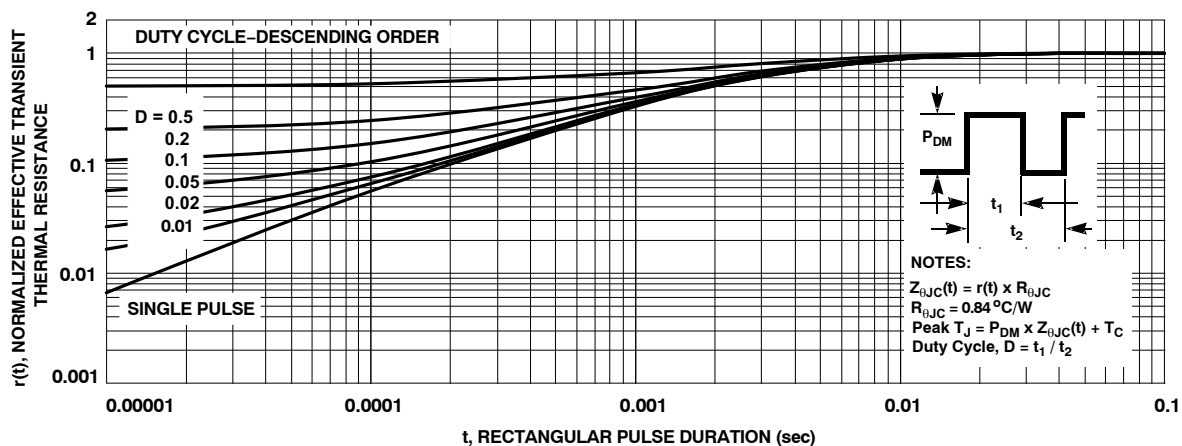


Figure 14. Junction-to-Case Transient Thermal Response Curve

ORDERING INFORMATION AND PACKAGE MARKING

Orderable Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTC080N120SC1	N/A	Die	Wafer	N/A	N/A	N/A

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